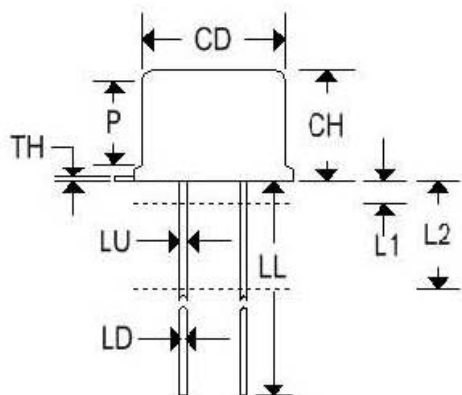
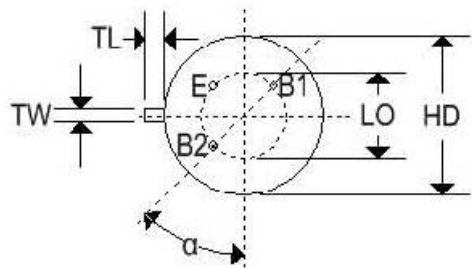


Transistors > Bipolar > Si NPN Power HF



Dim	TO-5			
	Inches		Millimeters	
	Min	Max	Min	Max
HD	0.335	0.370	8.510	9.400
CD	0.305	0.335	7.750	8.510
CH	0.240	0.260	6.100	6.600
LL	1.500	-	38.100	-
LD	0.016	0.021	0.410	0.530
LU	0.016	0.019	0.410	0.480
P	0.100	-	2.540	-
TL	0.029	0.045	0.740	1.140
TW	0.028	0.034	0.710	0.860
TH	0.009	0.125	0.230	3.180
LO	0.141 NOM		3.590 NOM	
α	45°TP		45°TP	

SPECIFICATIONS	Value	Unit
Military Grade	N	---
V_{BR} CEO	60	V
V_{BR} CBO	80	V
I_C Maximum	700	mA
Absolute Max. Power Diss.	5.0	W
Maximum Operating Temp.	200	°C
I_{CBO} Maximum	250	nA
@ V_{CBO} Test Condition	60	V
h_{FE} Min. Current Gain.	50	β
h_{FE} Max. Current Gain.	250	β
@ I_C Test Condition	150	mA
@ V_{CE} Test Condition	10	V
f_T Min. Transition Freq.	100	MHz
@ I_C Test Condition	50	mA
@ V_{CE} Test Condition	10	V
V_{CE} sat Max.	0.30	V
@ I_C Test Condition	150	mA
@ I_B Test Condition	15	mA
Package Style	TO-5	---
Mounting Style	T	---

